

## EAST Search History

| Ref # | Hits | Search Query                                                                                                                                                                   | DBs                                                               | Default Operator | Plurals | Time Stamp       |
|-------|------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------|------------------|---------|------------------|
| S1    | 2480 | ((438/455) or (438/458) or (438/479)).CCLS.                                                                                                                                    | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/01/31 16:24 |
| S2    | 836  | S1 and (soi or (silicon adj on adj insulator\$1))                                                                                                                              | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/06/09 17:39 |
| S3    | 94   | S2 and (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/01/31 16:25 |
| S4    | 23   | S3 and (delaminat\$3 or (smart near2 cut))                                                                                                                                     | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/01/31 16:32 |
| S5    | 1705 | 438/455                                                                                                                                                                        | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/01/31 16:24 |
| S6    | 2753 | ((438/455) or (438/458) or (438/479)).CCLS.                                                                                                                                    | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/01/31 16:24 |
| S7    | 2753 | ((438/455) or (438/458) or (438/479)).CCLS.                                                                                                                                    | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/01/31 16:28 |
| S8    | 947  | S7 and (soi or (silicon adj on adj insulator\$1))                                                                                                                              | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/01/31 16:31 |

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|     |     |                                                                                                                                                                                                                                                     |                                                                   |    |    |                  |
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| S9  | 2   | S8 and (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) near2 (wafer\$1 of substrate\$1))) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 16:29 |
| S10 | 2   | S7 and (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) near2 (wafer\$1 of substrate\$1))) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 16:30 |
| S11 | 104 | (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) near2 (wafer\$1 of substrate\$1)))        | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:00 |
| S12 | 30  | S11 and ("SOI" or (silicon adj on adj insulator\$1))                                                                                                                                                                                                | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:35 |
| S13 | 3   | S12 and (delaminat\$3 or (smart near2 cut))                                                                                                                                                                                                         | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 16:35 |
| S14 | 3   | S13 not S7                                                                                                                                                                                                                                          | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 16:35 |
| S15 | 0   | S13 not S12                                                                                                                                                                                                                                         | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 16:35 |

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|     |     |                                                                                                                                                                                                                                            |                                                                   |    |    |                  |
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| S16 | 27  | S12 not S13                                                                                                                                                                                                                                | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 16:35 |
| S17 | 66  | (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near2 wafer\$1) near ((base or support or handle) adj (wafer\$1 of substrate\$1))) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:01 |
| S18 | 207 | ((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near10 ((base or support or handle) adj wafer\$1)                                   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:07 |
| S19 | 34  | S18 and S7                                                                                                                                                                                                                                 | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:11 |
| S20 | 2   | ((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) adj ((base or support or handle) adj wafer\$1)                                      | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:07 |
| S21 | 147 | ((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) or epitaxial or (nitrogen adj dop\$3) or (hydrogen adj anneal\$3) or (intrinsic adj getter\$3)) near5 ((base or support or handle) adj wafer\$1)                                    | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:30 |
| S22 | 0   | S19 not S18                                                                                                                                                                                                                                | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:11 |

## EAST Search History

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| S23 | 173 | S18 not S19                                                                                                                                                                                                                                                                       | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:11 |
| S24 | 40  | (((fz or (float\$3 adj zone adj melt\$3 adj method\$1)) adj wafer\$1) or (epitaxial adj wafer\$1) or ((nitrogen adj dop\$3) adj wafer\$1) or ((hydrogen adj anneal\$3) adj wafer\$1) or ((intrinsic adj getter\$3) adj wafer\$1)) same ((base or support or handle) adj wafer\$1) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:35 |
| S25 | 34  | S24 and ("SOI" or (silicon adj on adj insulator\$1))                                                                                                                                                                                                                              | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/01/31 17:36 |